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| APPLICATION NO   | ). I                  | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO.          | CONFIRMATION NO. |
|--|-----------------------|-------------|----------------------|------------------------------|------------------|
| 10/076,154   | 10/076,154 02/14/2002 |             | Yoshinori Hino       | 10417-118001/<br>F51-142893M | 8619             |
| 26211  | 7590                  | 04/05/2004  |                      | EXAMINER                     |                  |
|  |                       | SON P.C.    | TRAN, TAN N          |                              |                  |
| 45 ROCKEFELLER PLAZA, SUITE 2800<br>NEW YORK, NY 10111 |                       |             |                      | ART UNIT                     | PAPER NUMBER     |
|  | <b>,</b>              |             |                      | 2826                         |                  |
|  |                       |             |                      | DATE MAILED: 04/05/200       | 4                |

Please find below and/or attached an Office communication concerning this application or proceeding.

| <u>•</u>   |  | - AV   |  |  |  |  |
|--|--|--|--|--|--|--|
|  | Application No.  | Applicant(s)   |  |  |  |  |
|  | 10/076,154   | HINO ET AL.  |  |  |  |  |
| Office Action Summary  | Examiner   | Art Unit   |  |  |  |  |
|  | TAN N TRAN   | 2826   |  |  |  |  |
| The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply   |  |  |  |  |  |  |
| A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period v  - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).   | 36(a). In no event, however, may a reply be ti<br>y within the statutory minimum of thirty (30) da<br>vill apply and will expire SIX (6) MONTHS from<br>, cause the application to become ABANDONI | mely filed ys will be considered timely. n the mailing date of this communication. ED (35 U.S.C. § 133). |  |  |  |  |
| Status   |  |  |  |  |  |  |
| 1)⊠ Responsive to communication(s) filed on <u>amer</u>  | ndment filed on 12/10/03 and 12  | <u>/15/03</u> .  |  |  |  |  |
|  | action is non-final.   | <del></del>  |  |  |  |  |
| 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is   |  |  |  |  |  |  |
| closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.  |  |  |  |  |  |  |
| Disposition of Claims  |  |  |  |  |  |  |
| <ul> <li>4)  Claim(s) 1-17,21-23,28 and 31-37 is/are pendidaa) Of the above claim(s) 1-17 is/are withdrawn</li> <li>5)  Claim(s) 22 is/are allowed.</li> <li>6)  Claim(s) 21,28 and 31-37 is/are rejected.</li> <li>7)  Claim(s) 23 is/are objected to.</li> <li>8)  Claim(s) are subject to restriction and/o</li> </ul>  | from consideration.  |  |  |  |  |  |
| Application Papers   |  |  |  |  |  |  |
| 9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) accomplicated and accomplicated and accomplicated and accomplicated to accomplicate and accomplicated and accomplicated and accomplicated and accomplicated and accomplicated accomplicate | epted or b) objected to by the drawing(s) be held in abeyance. So ion is required if the drawing(s) is of  | ee 37 CFR 1.85(a).<br>Djected to. See 37 CFR 1.121(d).   |  |  |  |  |
| Priority under 35 U.S.C. § 119   |  |  |  |  |  |  |
| 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  a) All b) Some * c) None of:  1. Certified copies of the priority documents have been received.  2. Certified copies of the priority documents have been received in Application No  3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).  * See the attached detailed Office action for a list of the certified copies not received.  |  |  |  |  |  |  |
| Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date  | 4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal I 6) Other:  |  |  |  |  |  |

## **DETAILED ACTION**

1. The indicated allowability of claims 21,28,31-33 is withdrawn in view of the newly discovered reference(s) to claims 21,28,31-33. Rejections based on the newly cited reference(s) follow.

## Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 21,28,31-37 are rejected under 35 U.S.C. 102(e) as being anticipated by Harada et al. (6,476,491).

With regard to claims 21,31,34, Harada et al. discloses a semiconductor substrate 1; a gate oxide film 3 provided over the semiconductor substrate 1; a gate electrode 4 formed on the gate oxide film 3; a source/drain region 5 formed in the semiconductor substrate 1 and disposed adjacent to the gate electrode 4; a lower layer wiring 21 connected to the source/drain region 5 with contact; an interlayer insulating film 22 covering the lower layer wiring 21; a via hole 24 formed in an interlayer insulating film 22; and an upper layer wiring 25 having an intermetallic compound layer 101 serves as a pad portion wherein the intermetallic compound layer 101 disposed over the interlayer insulating film 22 and connected to the lower layer wiring 21

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through via hole 24, and wherein no hole connecting the upper layer wiring 25 and the lower layer wiring is formed under the intermetallic compound layer 101. (Note fig. 1 of Harada et al.).

With regard to claims 28,35, Harada et al. discloses the interlayer insulating layer 22 is provided with additional holes 23 to couple the upper layer wiring 25 to the lower layer wiring 21. (Note fig. 1 of Harada et al.).

With regard to claim 32,33,36, Harada et al. discloses a bump electrode provided at the intermetallic compound layer 101 serves as a pad portion of the bump electrode. (Note lines 19-21, column 18, fig. 1 of Harada et al.).

With regard to claim 37, Harada et al. discloses the lower layer wiring 21 arranged below the bump electrode. (Note lines 19-21, column 18, fig. 1 of Harada et al.).

## Allowable Subject Matter

3. Claim 23 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Claim 23 is allowable over the prior art of record, because none of these references disclose or can be combined to yield the claimed invention such as the low concentration region extends shallowly to a surface layer under the gate electrode to connect to the source/drain region and to contact the semiconductor region as recited in claim 23.

4. Claim 22 is allowable over the prior art of record, because none of these references disclose or can be combined to yield the claimed invention such as a low concentration region of the same conductivity type as the source/drain region formed under the gate electrode so as to

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connected to the source/drain region and to contact the semiconductor region as recited in claim

22.

Response to Amendment

5. Applicant's arguments with respect to claims 21,28,31-37 have been considered but are

moot in view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communication from the examiner

should be directed to Tan Tran whose telephone number is (571) 272-1923. The examiner can

normally be reached on M-F 8:30AM-5PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone numbers for the

organization where this application or proceeding is assigned are (703) 872-9306 for regular

communications and (703) 872-9306 for after final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is (703) 305-3900.

TT

Mar 2004

Minhloan Tran Primary Examiner

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